Probing Noise in Flux Qubits via Macroscopic Resonant Tunneling

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Macroscopic resonant tunneling between the two lowest lying states of a bistable RF-SQUID is used to characterize noise in a flux qubit. Measurements of the incoherent decay rate as a function of flux bias revealed a Gaussian shaped profile that is not peaked at the resonance point, but is shifted to a bias at which the initial well is higher than the target well. The r.m.s. amplitude of the noise, which is proportional to the decoherence rate $1/T_2^*$, was observed to be weakly dependent on temperature below 70 mK. Analysis of these results indicates that the dominant source of low frequency $(1/f)$ flux noise in this device is a quantum mechanical environment in thermal equilibrium.

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The viability of any scalable quantum computing architecture is highly dependent upon its performance in the presence of noise. In the case of superconducting qubits it has been shown that low frequency $(1/f)$ flux noise is of particular concern [\[1\]](#page-3-2). Furthermore, evidence suggests that such devices generically couple to an ensemble of effective 2-level systems (TLS) that may be materials defects [\[2\]](#page-3-3). A number of theories exist that attempt to correlate these two observations [\[3\]](#page-3-4), however it is not certain whether the TLS observed in spectroscopy experiments are the dominant source of low frequency noise in these devices [\[4](#page-3-5)]. The development of additional experimental probes of low frequency noise will prove critical in the quest to build reliable superconductor-based quantum computing hardware. In this article we demonstrate a new experimental procedure for quantifying low frequency flux noise in RF-SQUID qubits. The procedure developed herein complements other approaches to using qubits as spectrometers for studying noise [\[5\]](#page-3-6).

Macroscopic resonant tunneling (MRT) [\[6](#page-3-7), [7\]](#page-3-8) is an important probe of quantum effects in Josephson junctionbased devices. In an MRT experiment flux tunnels between two wells of a double well potential when energy levels are aligned. The tunneling rate and width of the tunneling region are strongly influenced by the environment. The effect of flux noise on the two lowest energy levels can be described using an effective Hamiltonian

$$
\mathcal{H}_{\text{eff}} = -\frac{1}{2} \left[\epsilon \sigma_z + \Delta \sigma_x \right] - \frac{1}{2} Q_z \sigma_z \,, \tag{1}
$$

where ϵ is the bias energy between the wells, Δ is the tunneling amplitude, Q_z is an operator that acts on the low frequency modes of the environment and $\sigma_{x(z)}$ are Pauli matrices. In general, a transverse coupling to the environment should also exist but it is believed to be subdominant to the longitudinal coupling in flux qubits [\[8\]](#page-3-9). It is demonstrated that the experimental results presented herein are consistent with this expectation.

A theoretical analysis of MRT in the presence of low frequency (non-Markovian) flux noise was reported in Ref. [\[9](#page-3-10)]. The transition rate Γ_{01} from state $|0\rangle$ to state |1\; (both eigenfunctions of σ_z with eigenvalues ∓ 1 , respectively) was found to be

$$
\Gamma_{01}(\epsilon) = \sqrt{\frac{\pi}{8}} \frac{\Delta^2}{W} \exp\left[-\frac{(\epsilon - \epsilon_p)^2}{2W^2}\right] , \qquad (2)
$$

$$
\epsilon_p = \mathcal{P} \int_{-\infty}^{\infty} d\omega \frac{S(\omega)}{\omega} , \quad W = \left[\int_{-\infty}^{\infty} d\omega S(\omega)\right]^{1/2} ,
$$

where $S(\omega) = \frac{1}{2\pi} \int dt \ e^{i\omega t} \langle Q_z(t) Q_z(0) \rangle$ is the unsym-metrized noise spectral density [\[10\]](#page-3-11). Γ_{10} is obtained by substituting $\epsilon_p \rightarrow -\epsilon_p$. Equation [\(2\)](#page-0-0) is valid provided the noise spectrum is peaked at low frequency and the integrals defining ϵ_p and W are finite [\[9](#page-3-10)]. The latter constraint may require low and high frequency cutoffs.

The quantities ϵ_p and W represent the energy shift and width of a Gaussian shaped tunneling rate, respectively. W is the r.m.s. amplitude of the noise and ϵ_p is a measure of the asymmetry of $S(\omega)$. For a classical noise source $S(\omega) \approx S(-\omega)$, hence $\epsilon_p = 0$. For a quantum source $S(\omega)$ need not be symmetric and therefore $\epsilon_p \neq 0$. In thermal equilibrium at temperature T_{eff} the fluctuation-dissipation theorem dictates that $S(\omega)$ can be expressed as a sum of symmetric and antisymmetric components $S(\omega) = S_s(\omega) + S_a(\omega)$, where $S_s(\omega) =$ $S_a(\omega)$ coth $(\omega/2T_{\text{eff}})$ $(\hbar/k_B \equiv 1)$. If $S_a(\omega)$ is sharply peaked near $\omega = 0$ then it can be shown that

$$
W^2 \approx \mathcal{P} \int_{-\infty}^{\infty} d\omega S_a(\omega) (2T_{\text{eff}}/\omega) = 2T_{\text{eff}}\epsilon_p . \qquad (3)
$$

The width W is an important parameter in adiabatic quantum computation [\[11\]](#page-3-12) as it defines the precision to which a target Hamiltonian can be specified in the logical basis defined by the eigenstates of σ_z . From the perspective of gate model quantum computation W is closely

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related to the decoherence time T_2^* in the energy basis defined by the eigenstates of Eq. (1) . For a low frequency environment the decay due to dephasing has the form $e^{-t^2/2T_2^{*^2}}$, where $1/T_2^* = \cos(\eta) W$ and $\eta = \arctan(\Delta/\epsilon)$.

To demonstrate the MRT method for characterizing low frequency noise we employed an RF-SQUID qubit [\[12,](#page-3-13) [18](#page-3-14)]. Previous experimental observations of MRT in RF-SQUIDs have been limited to tunneling into higher energy levels with and without the help of microwave activation [\[7,](#page-3-8) [13\]](#page-3-15). In this paper we examine MRT between the two lowest energy levels of an RF-SQUID. Measurements of directional tunneling rates Γ_{01} and Γ_{10} are used to extract quantitative information regarding $S(\omega)$.

A schematic of a compound Josephson junction (CJJ) RF-SQUID is shown in the inset of Fig. [1\(](#page-1-0)a). It consists of a main loop and CJJ loop subjected to external flux biases Φ_x^q and Φ_x^{cjj} , respectively. The CJJ loop is interrupted by two nominally identical Josephson junctions connected in parallel with total capacitance C^q and critical current I_c^q . The CJJ and main loop possess inductances L^{cjj} and L^q , respectively. If $L^{cjj} \ll L^q$ then the RF-SQUID Hamiltonian can be written as

$$
\mathcal{H}_{\rm rf}(\Phi^q, \Pi^q) = \frac{1}{2C^q} (\Pi^q)^2 + U(\Phi^q) , \qquad (4)
$$

$$
U(\Phi^q) = \frac{(\Phi^q-\Phi_x^q)^2}{2L^q} - E_J \cos\biggl[\frac{\pi\Phi_x^{cjj}}{\Phi_0}\biggr] \cos\biggl[\frac{2\pi\Phi^q}{\Phi_0}\biggr]~,
$$

where Φ^q represents the total flux threading the main loop, Π^q is the conjugate momentum, $E_J \equiv \Phi_0 I_c^q/2\pi$ and $\Phi_0 = h/2e$. This device can be operated as a qubit for $\Phi_x^{cjj} \in [0.5, 1]\Phi_0$ and $\Phi_x^q \approx 0$. Denoting the ground and first excited state of $\mathcal{H}_{\rm rf}$ at $\Phi_x^q = 0$ by $|g\rangle$ and $|e\rangle$, respectively, the qubit states can be expressed as $|0\rangle = (|g\rangle + |e\rangle)/\sqrt{2}$ and $|1\rangle = (|g\rangle - |e\rangle)/\sqrt{2}$. The bias energy of Eq. [\(1\)](#page-0-1) is given by $\epsilon = 2 \left| I_g^q \right| \Phi_x^q$, where the persistent current $|I_p^q| \equiv |\langle 0| \Phi^q / L^q |0 \rangle| = |\langle 1| \Phi^q / L^q |1 \rangle|.$ The tunneling amplitude of Eq. [\(1\)](#page-0-1) is given by $\Delta =$ $\langle e | \mathcal{H}_{\rm rf} | e \rangle - \langle g | \mathcal{H}_{\rm rf} | g \rangle$. Both $\left| I_p^q \right|$ and Δ are controlled by Φ_x^{cjj} . Maximum $\Delta \sim \omega_p$, where ω_p is the plasma frequency of the RF-SQUID, is obtained at $\Phi_x^{cjj} = \Phi_0/2$. For $\Phi_x^{cjj} \approx \Phi_0$ one expects $\Delta \to 0$ and the system becomes localized in $|0\rangle$ or $|1\rangle$. In this latter regime $|I_p^q|$ generates a measurable amount of flux that can be detected via an inductively coupled DC-SQUID read-out (not shown) as described in Ref. [\[15](#page-3-16), [16](#page-3-17)].

The CJJ RF-SQUID from which the data presented herein were obtained was fabricated on an oxidized Si wafer using a Nb trilayer process with wiring layers isolated by sputtered $SiO₂$. The device parameters were $L^q = 661 \pm 6 \text{ pH}, C^q = 146 \pm 3 \text{ fF} \text{ and } I_c^q = 1.95 \pm 0.05 \mu\text{A}.$ L^q was measured using a breakout structure and C^q was inferred from the value of L^q and measurements of the MRT peak spacing [\[7\]](#page-3-8). From the MRT spacing we also determined $\omega_p \sim 10 \text{ GHz}$. The DC-SQUID was observed

FIG. 1: (Color online) (a) MRT flux control bias sequence as a function of time. Inset depicts a CJJ RF-SQUID subjected to the external biases Φ_x^{cjj} and Φ_x^q . Sense of the macroscopic persistent current states $|0\rangle$ (counterclockwise) and $|1\rangle$ (clockwise) are noted. (b) Evolution of the qubit potential $U(\Phi^q)$.

to have a maximum switching current $I_{\text{sw}}^{\text{DC}} = 1.9 \pm 0.1 \,\mu\text{A}$ and the readout-qubit mutual inductance was $M_{\text{ro-a}} =$ 16.7 ± 0.2 pH. The device was mounted in an Al box in a dilution refrigerator and all on-chip cross couplings were calibrated in-situ as described in Ref. [\[16](#page-3-17)].

Our experimental procedure is a variant of the MRT technique first developed by Rouse, Han, and Lukens [\[7\]](#page-3-8). We exploit Φ_x^{cjj} to modulate Δ using a bias line with bandwidth ∼ 5 MHz. A depiction of the control sequence and the evolution of the qubit potential $U(\Phi^q)$ are shown in Fig. [1.](#page-1-0) The state of the qubit is initialized by setting $\Phi_x^{cjj} \approx \Phi_0/2$ (i) and then tilting $U(\Phi^q)$ via Φ_x^q to an initial value of Φ_i^q (ii). Slowly raising Φ_x^{cjj} to Φ_0 in the presence of the tilt traps the system in its groundstate (iii). With tunneling suppressed, Φ_x^q is reset to a target value $\Phi_f^{\mathbf{q}}$ (iv). Thereafter Φ_x^{cjj} is lowered (v) to Φ_f^{cjj} for a prescribed amount of time t during which the system can tunnel from the initial state to the lowest lying state in the opposite well (vi). Raising Φ_x^{cjj} (vii) to Φ_0 then localizes the qubit state in $|0\rangle$ or $|1\rangle$ (viii) which can then be distinguished by a single shot readout. The probability of tunneling from the initial to final state is then measured as a function of t and Φ_f^q . For a given Φ_f^q the probability of the system being found in $|0\rangle$ can be calculated from

FIG. 2: (Color online) (a) MRT from the initial state $|0\rangle$ versus t at $T_{\text{th}} = 28 \text{ mK}$. Results are shown for $\Phi_f^q = -0.488 \text{ m}\Phi_0$ (solid squares), $-0.014 \,\mathrm{m}\Phi_0$ (hollow circles) and $0.554 \,\mathrm{m}\Phi_0$ (solid circles). Slopes of the linear fits yield $-\Gamma_{01}(\Phi_f^q)$. (b) Γ_{01} (hollow) and Γ_{10} (solid) versus Φ_f^q at $T_{th} = 28 \text{ mK}$. The peaks nearest $\Phi_f^q = 0$ have been fit to Eq. [\(2\)](#page-0-0).

balancing Γ_{01} and Γ_{10} : $dP_0/dt = -\Gamma_{01}P_0(t) + \Gamma_{10}P_1(t)$, where $P_0(t) + P_1(t) = 1$. In the limit $t \to 0$ the system starts in a definite state and this expression reduces to $dP_0/dt = -\Gamma_{01} (P_0(0) = 1)$ or $\Gamma_{10} (P_1(0) = 1)$.

The results shown herein were generated using a value of Φ_f^{cjj} for which we measured $|I_p^q| = 0.56 \pm 0.02 \,\mu\text{A}.$ This particular target CJJ bias was chosen as 1/Γ varies by nearly four orders of magnitude $(10 \,\mu s \rightarrow 100 \,\text{ms})$ as a function of Φ_f^q in the vicinity of $\Phi_f^q = 0$, which then takes full advantage of the dynamic range of our apparatus. Using the calibrated device parameters and Eq. [\(4\)](#page-1-1) it was determined that the above mentioned value of $|I_p^q|$ could be achieved for $\Phi_f^{cjj} = 0.606 \pm 0.001 \Phi_0$. The tunnel splitting was then estimated to be $\Delta_0 = 0.10_{-0.07}^{+0.28}$ mK. The asymmetric error bars on Δ_0 are a consequence of its exponential sensitivity to errors in L^q , C^q , and I_c^q .

We have measured $P_0(\Phi_x^q, t)$ for $\Phi_f^q \in [-3, 3]$ m Φ_0 and for the qubit initialized with $P_0(0) = 1$ and $P_1(0) = 1$. Example decay data are shown in Fig. [2\(](#page-2-0)a) for $P_0(0)$ = 1 at three nominal target values of Φ_f^q and the device

FIG. 3: (Color online) (a) Temperature dependence of ϵ_p (solid) and W (hollow). W has been fit to a line (dotted) and ϵ_p to a power law C/T_{th}^{α} (dashed). (b) $T_{\text{eff}} = W^2/2\epsilon_p$ versus T_{th} . Dashed line indicates $T_{\text{eff}} = T_{\text{th}}$.

thermalized at $T_{\rm th}=28\, \rm mK.$ A summary of initial decay rates as a function of Φ_f^q for both initializations is shown in Fig. [2\(](#page-2-0)b). We have independently calibrated $\Phi_f^q = 0$ by measuring the population statistics in the limit $t\rightarrow\infty$ and observing that the center of the resultant thermal distribution is independent of initial state. Fitting of the distribution to $P_0(t\rightarrow\infty) = \frac{1}{2} [1 - \tanh(\epsilon/2T_{\text{th}})]$ yields $T_{\rm th}$. Note that Γ_{01} and Γ_{10} are mirror images across $\Phi_f^{\rm q} = 0$ but both are asymmetric about this point. The data suggest that Γ_{01} and Γ_{10} consist of broad peaks that are displaced away from $\Phi_f^q = 0$ in the direction opposite that in which the system was initialized. These peaks can be attributed to splitting by noise of a single MRT peak corresponding to tunneling between the two lowest lying states of the bistable RF-SQUID. This splitting indicates that $S_a(\omega) \neq 0$. Beyond $|\Phi_f^{\rm q}| \gtrsim 2 \,{\rm m}\Phi_0$, the decay rates increase due to MRT between the initialized state and the first excited state in the opposing well.

The data in Fig. [2\(](#page-2-0)b) have been fit to Eq. (2) using W, ϵ_p and Δ as free parameters. The fact that the tunneling rate can be fit to a Gaussian lineshape indicates that the noise is dominated by low frequency components. We re-

FIG. 4: Temperature dependence of ∆. Dashed line is a fit.

peated the measurements for five different temperatures and the resultant fit values of ϵ_p and W are summarized in Fig. [3\(](#page-2-1)a). Here it can be seen that W is only weakly dependent upon T . Fitting these results to a line indicates that $W(T \to 0) \approx 80$ mK. This conclusion corroborates the observations presented in Ref. [\[17\]](#page-3-18) from phase qubits in which the Rabi decay time is observed to have a weak T dependence as $T \to 0$. In contrast, ϵ_p varies strongly with T, behaving as $\sim 1/T_{\rm th}^{0.80 \pm 0.05} \approx 1/T$. Finally, an explicit demonstration of the self-consistency of our analysis is shown in Fig. [3\(](#page-2-1)b) where T_{eff} obtained from Eq. [\(3\)](#page-0-2) is plotted versus T_{th} . Agreement between T_{eff} and T_{th} demonstrates the equilibrium nature of the low frequency flux noise in our system.

Figure [4](#page-3-19) shows the variation of Δ with temperature. Note that the results are comparable to Δ_0 as estimated from qubit parameters, but that the uncertainty in Δ_0 makes it difficult to draw any quantitative conclusions from such a comparison. Nonetheless, the data suggest that $\Delta \propto T_{\text{th}}$. It is known that high frequency flux noise can lead to renormalization of Δ [\[10](#page-3-11)] and that a polynomial dependence of Δ on T results if the environment possesses an ohmic density of states at high frequency [\[18\]](#page-3-14). A similar combination of sharply peaked low frequency noise, as required for Eq. [\(2\)](#page-0-0), and ohmic high frequency noise has been reported for other qubits [\[1](#page-3-2), [19\]](#page-3-20).

In addition to studying MRT between the two lowest lying states, we have measured MRT from the lowest state in the initial well to higher levels in the final well. It was observed that the tunneling rate versus Φ_f^q could be fit to a lineshape whose width increased monotonically with the number of levels below the target level, as anticipated in Refs. [\[6\]](#page-3-7) and [\[9](#page-3-10)]. The width of the peak for tunneling to the 50-th level in the final well was roughly twice that for the lowest order MRT peak. This weak dependence on the number of states below the target level indicates the relative weakness of $S(\omega)$ at high frequency.

Conclusions: Measurements of MRT between the two

lowest energy states of a bistable RF-SQUID have been used to characterize flux noise. Analysis indicates that the noise source is a quantum mechanical environment in thermal equilibrium whose spectral density is sharply peaked at low frequency.

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